

**(19) World Intellectual Property
Organization
International Bureau**



(43) International Publication Date
9 September 2005 (09.09.2005)

PCT

(10) International Publication Number
WO 2005/083770 A1

(51) International Patent Classification⁷: H01L 21/336

(21) International Application Number:
PCT/KR2005/000574

(22) International Filing Date: 2 March 2005 (02.03.2005)

(25) Filing Language: Korean

(26) Publication Language: English

(30) Priority Data:
10-2004-0014036 2 March 2004 (02.03.2004) KR

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(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM,

AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG,
MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH,
PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

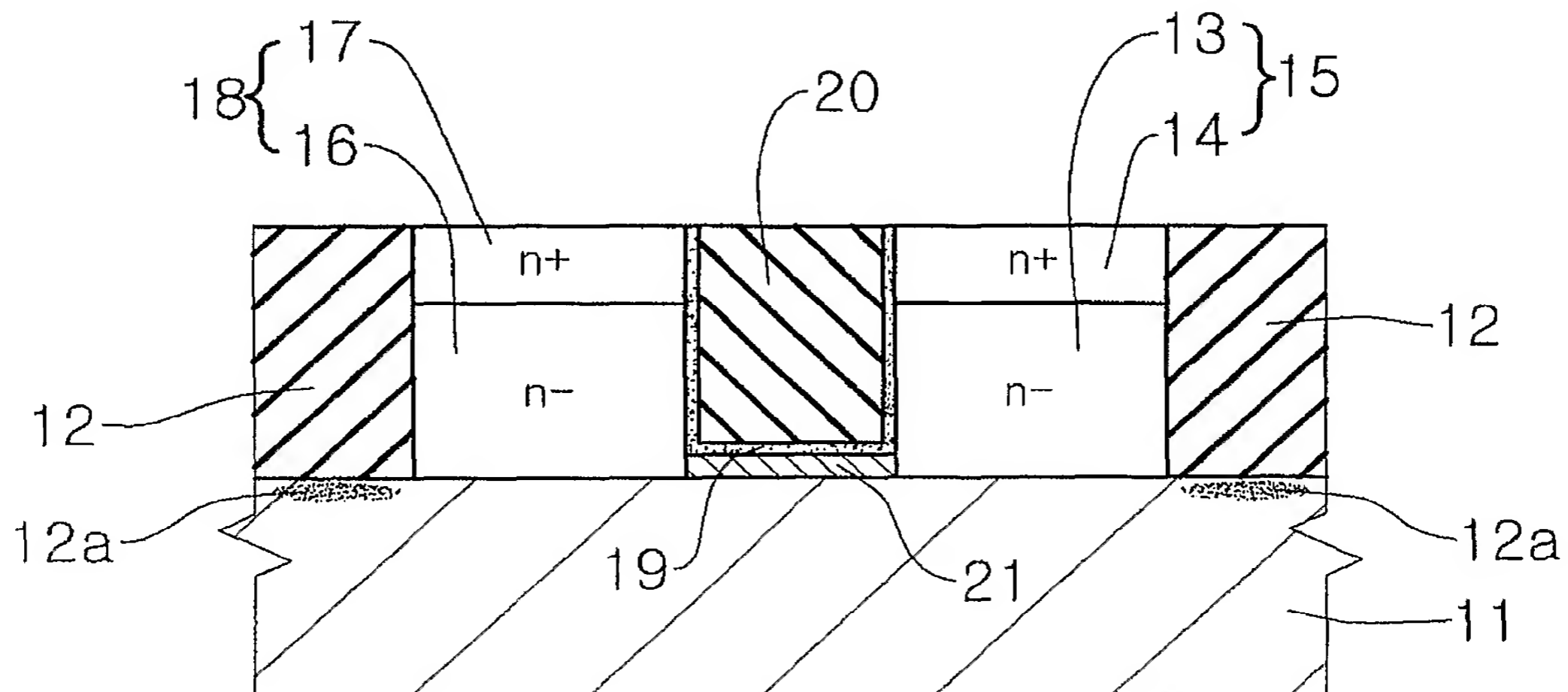
(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: SEMICONDUCTOR DEVICE OF HIGH BREAKDOWN VOLTAGE AND MANUFACTURING METHOD THEREOF



(57) Abstract: Disclosed are a semiconductor device of high breakdown voltage and a method manufacturing the same. According to the invention, it is possible to previously prevent an increase size of the device due to a separation of a high concentration impurity layer and a gate electrode pattern by embedding the gate electrode pattern in a bottom of a semiconductor substrate, and sequentially stacking a low concentration impurity layer and a high concentration impurity layer for source/drain diffusion layers on both sides of the gate electrode pattern, thereby allowing the high concentration impurity layer to easily secure a voltage drop areas necessary for itself without being spaced from the gate electrode pattern.

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